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(54) Title: CARBON MASK DEPOSITION

(57) Abstract: Examples are disclosed that relate to depositing a carbon mask to thicken a partially etched mask. One example provides a method comprising forming a mask layer on a substrate, and etching the substrate to partially form one or more etched features, the etching of the substrate also causing etching of the mask layer. The method further comprises, after etching a portion of the one or more etched features but before completing etching of the one or more etched features, depositing, by plasma-enhanced chemical vapor deposition (PECVD), a carbon mask over the mask layer.

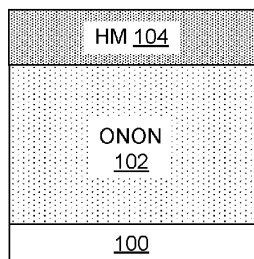


FIG. 1A

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